



<b>Substitute for form 1449A/PTO</b> <b>INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		<b>Complete if Known</b>			
		Application Number	09/197,534		
		Filing Date	November 23, 1998		
		First Named Inventor	Shunpei YAMAZAKI et al.		
		Art Unit	2823		
		Examiner Name	William D. Coleman		
Sheet	1	of	1	Attorney Docket Number	740756-1894

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US-			
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FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
		JP 2-187294	07/23/1990	KAJIKAWA		AB

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		Itoga et al. "Laser Re-Crystallization Utilizing Beam Homogenizing Optical System" Japan Society of Applied Physics, Proceedings of 48 <sup>th</sup> Annual Meetings, 2 <sup>nd</sup> Part, 18 p-6-N-6, P. 537 (1987)	

Examiner Signature		Date Considered	3/19/04
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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Submitted with Office Action 15, 2000

Sheet 1 of 4

Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty.Docket No. 0756-1894		Serial No. 09/197,534	
<b>INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)				Applicant Shunpei Yamazaki et al.			
				Filing Date November 23, 1998		Group 2874	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
		3,667,832	06/72	Kitano et al.			
		4,436,557	03/13/84	Wood et al.			
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		4,733,944	03/29/88	Fahlen et al.			
		4,769,750	09/06/88	Matsumoto et al.			
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		Document Number	Date	Country	Class	Subclass	Translation Yes No
		176715	03/89	Japan			Abst.
		220681	01/24/90	Japan			Abst.
		2-73623	03/13/90	Japan			Full
		1187814	07/27/89	Japan			Abst.
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	Pennington, K.S. et al., "CCD Imaging Array Combining Fly's Eye Lens with TDI for Increasing Light-gathering Ability", IBM Technical Disclosure Bulletin, Vol. 21, No.2, July 1978, pp. 857-858.						
	"Crystallization of Amorphous Silicon by Excimer Laser Annealing with a Line Shape Beam Having A Gaussian Profile", Young Min Jhon et al., Jpn. J. Appl. Phys. Vol. 33 (1994), pp. L1438-1441						
	"Enlargement of Poly-Si Film Grain Size by Excimer Laser Annealing and its Application to High-Performance Poly-Si Thin Film Transistor", Hiroyuki Kuriyama et al., Jpn. J. App. Phys., Vol. 30, No. 12B, December, 1991, pp. 3700-3703.						
	"Formation of p-n Junctions and Silicides in Silicon Using a High Performance Laser Beam Homogenization System", M. Wagner et al., Applied Surface Science 43 (1989), pp. 260-263.						
Examiner				Date Considered 3/19/04			
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(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark OfficeAtty. Docket No.  
0756-1894Serial No.  
09/197,534

## INFORMATION DISCLOSURE STATEMENT



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Applicant  
Shunpei Yamazaki et al.Filing Date  
November 23, 1998Group  
2874





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						Yes	No
	1239837	12/18/89	Japan			Abst.	
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	"Improving the Uniformity of Poly-Si Films Using a New Excimer Laser Annealing Method for Giant-Microelectronics", Hiroyuki Kuriyama et al., Jpn. J. Appl. Phys. Vol. 31, Part 1, No. 12B, December 1992, pp. 4450-4554.
	"Lateral Grain Growth of Poly-Si Films with a Specific Orientation by an Excimer Laser Annealing Method", Hiroyuki Kuriyama et al., Jpn. J. Appl. Phys. Vol. 32 (1993), Pt. 1, No. 12B, pp. 6190-6195.
	"P-28: 3.7-in.-Diagonal STN-LCD with Stripe Electrode Patterns Fabricated by an Excimer-Laser Scribing System" T. Konuma et al., Semiconductor Energy Laboratory Co., Ltd., 550. SID 93 Digest.
	"Poly-Si by Excimer Laser Annealing with Solidification Process Control", Shigeru Noguchi et al., C-II, Vol. J76-C-II, No. 5, 1993, pp. 241-248.

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3/19/04

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	5,307,207	04/26/94	Ichihara			
	5,372,836	12/13/94	Imahashi et al.			
	5,413,958	05/09/95	Imahashi et al.			
	5,432,122	07/11/95	Chae			
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	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
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	64-76715	03/22/89	Japan			Full	
	5-8127318	10/20/83	Japan			Abst.	
	5-8191420	02/07/84	Japan			Abst.	

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

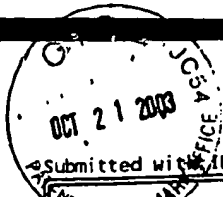
	Enlargement of Poly-Si film Grain Size by Excimer Laser Annealing and its Application to High-performance Poly-Si Thin Film Transistor", hiroyuki Kuriyama et al., Jpn J. App. Phys., Vol. 30, No. 12B, December, 1991, pp. 3700-3703.

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Submitted with IDS on June 15, 2000

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1449  
(Rev. 8-83)

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Patent and Trademark Office

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Document Number	Date	Country	Class	Subclass	Translation Yes No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)


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**Atty. Docket No.: 0756-1894**


**Serial No. 09/197,534**

Applicant: SHUNPEI YAMAZAKI et al.

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

## U.S. PATENT DOCUMENTS

Examiner Initial		Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date (if approp.)
		6,149,988	11/21/00	Shinohara et al.			

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**OTHER DOCUMENTS** (Including Author, Title, Relevant Pages, Date, Place of Publication)

6	Semiconductor World, Chapter 2, Active Element Array Forming Technology Annealing Apparatus, Excimer Laser Annealing Apparatus Leonix, October 1992, pp. 196-197

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**Date Considered**

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		US-			
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		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
		JP 60-005508 /	01/12/1985	KOICHI		AB
		JP 01-283917 /	11/15/1989	MICHIHIKO		AB
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		JP 57-083745 /	01/01/1982			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

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